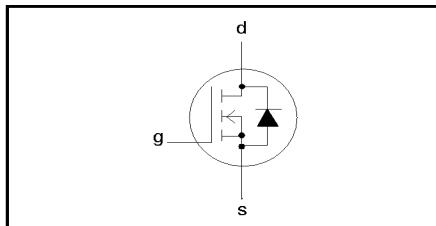


**N-channel TrenchMOS™ transistor
Logic level FET**
**PHP55N03LT, PHB55N03LT
PHD55N03LT**
FEATURES

- 'Trench' technology
- Very low on-state resistance
- Fast switching
- Low thermal resistance
- Logic level compatible

SYMBOL**QUICK REFERENCE DATA**

$V_{DSS} = 25 \text{ V}$
$I_D = 55 \text{ A}$
$R_{DS(ON)} \leq 14 \text{ m}\Omega (\text{V}_{GS} = 10 \text{ V})$
$R_{DS(ON)} \leq 18 \text{ m}\Omega (\text{V}_{GS} = 5 \text{ V})$

GENERAL DESCRIPTION

N-channel enhancement mode logic level field-effect power transistor in a plastic envelope using 'trench' technology.

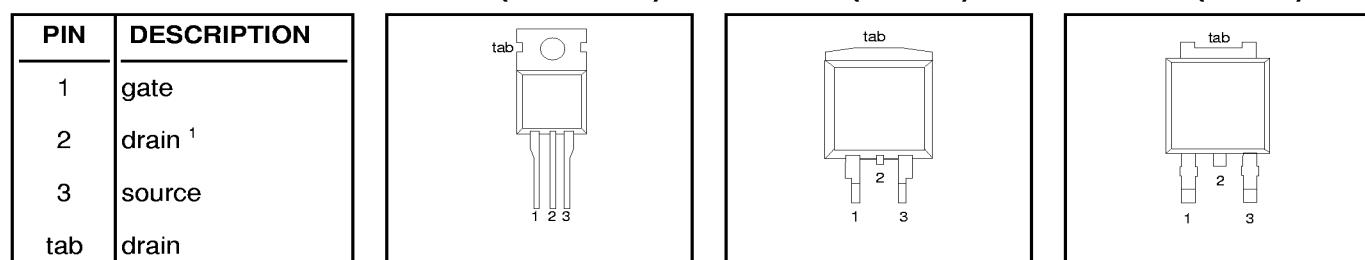
Applications:-

- High frequency computer motherboard d.c. to d.c. converters
- High current switching

The PHP55N03LT is supplied in the SOT78 (TO220AB) conventional leaded package.

The PHB55N03LT is supplied in the SOT404 (D²PAK) surface mounting package.

The PHD55N03LT is supplied in the SOT428 (DPAK) surface mounting package.

PINNING**SOT78 (TO220AB)****SOT404 (D²PAK)****SOT428 (DPAK)****LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DSS}	Drain-source voltage	$T_j = 25^\circ\text{C}$ to 175°C	-	25	V
V_{DGR}	Drain-gate voltage	$T_j = 25^\circ\text{C}$ to 175°C ; $R_{GS} = 20 \text{ k}\Omega$	-	25	V
V_{GS}	Gate-source voltage (DC)	-	± 15	± 15	V
V_{GSM}	Gate-source voltage (pulse peak value)	$T_j \leq 150^\circ\text{C}$	-	± 20	V
I_D	Drain current (DC)	$T_{mb} = 25^\circ\text{C}$	-	55	A
		$T_{mb} = 100^\circ\text{C}$	-	38	A
I_{DM}	Drain current (pulse peak value)	$T_{mb} = 25^\circ\text{C}$	-	220	A
P_{tot}	Total power dissipation	$T_{mb} = 25^\circ\text{C}$	-	103	W
T_j, T_{stg}	Operating junction and storage temperature	$T_{mb} = 25^\circ\text{C}$	-55	175	$^\circ\text{C}$

¹ It is not possible to make connection to pin:2 of the SOT404 or SOT428 packages.

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j\rightarrow mb}$	Thermal resistance junction to mounting base		-	-	1.45	K/W
$R_{th\ j\rightarrow a}$	Thermal resistance junction to ambient	SOT78 package, in free air SOT404 and SOT428 packages, pcb mounted, minimum footprint	- -	60 50	- -	K/W K/W

AVALANCHE LIMITING VALUE

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
W_{DSS}	Drain-source non-repetitive unclamped inductive turn-off energy	$I_D = 25\ A$; $V_{DD} \leq 15\ V$; $V_{GS} = 5\ V$; $R_{GS} = 50\ \Omega$; $T_{mb} = 25\ ^\circ C$	-	60	mJ

ELECTRICAL CHARACTERISTICS

$T_j = 25^\circ C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\ V$; $I_D = 0.25\ mA$;	25	-	-	V
$V_{GS(TO)}$	Gate threshold voltage	$T_j = -55^\circ C$	22	-	-	V
$R_{DS(ON)}$	Drain-source on-state resistance	$V_{DS} = V_{GS}$; $I_D = 1\ mA$	1	1.5	2	V
g_{fs}	Forward transconductance	$T_j = 175^\circ C$	0.5	-	-	V
I_{GSS}	Gate source leakage current	$T_j = -55^\circ C$	-	-	2.3	V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 10\ V$; $I_D = 25\ A$	-	11	14	$m\Omega$
		$V_{GS} = 10\ V$; $I_D = 25\ A$ (SOT428 package)	-	14	16	$m\Omega$
		$V_{GS} = 5\ V$; $I_D = 25\ A$	-	15	18	$m\Omega$
		$V_{GS} = 5\ V$; $I_D = 25\ A$; $T_j = 175^\circ C$	-	-	34	$m\Omega$
		$V_{DS} = 25\ V$; $I_D = 25\ A$	10	28	-	S
		$V_{GS} = \pm 5\ V$; $V_{DS} = 0\ V$	-	10	100	nA
		$V_{DS} = 25\ V$; $V_{GS} = 0\ V$;	-	0.05	10	μA
		$T_j = 175^\circ C$	-	-	500	μA
$Q_{g(tot)}$	Total gate charge	$I_D = 55\ A$; $V_{DD} = 15\ V$; $V_{GS} = 5\ V$	-	20	-	nC
Q_{gs}	Gate-source charge		-	8	-	nC
Q_{gd}	Gate-drain (Miller) charge		-	9	-	nC
$t_{d\ on}$	Turn-on delay time	$V_{DD} = 15\ V$; $I_D = 25\ A$	-	7	15	ns
t_r	Turn-on rise time	$V_{GS} = 10\ V$; $R_G = 5\ \Omega$	-	56	80	ns
$t_{d\ off}$	Turn-off delay time	Resistive load	-	57	80	ns
t_f	Turn-off fall time		-	38	50	ns
L_d	Internal drain inductance	Measured tab to centre of die	-	3.5	-	nH
L_d	Internal drain inductance	Measured from drain lead to centre of die (SOT78 package only)	-	4.5	-	nH
L_s	Internal source inductance	Measured from source lead to source bond pad	-	7.5	-	nH
C_{iss}	Input capacitance	$V_{GS} = 0\ V$; $V_{DS} = 20\ V$; $f = 1\ MHz$	-	1230	-	pF
C_{oss}	Output capacitance		-	354	-	pF
C_{rss}	Feedback capacitance		-	254	-	pF

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REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS

$T_j = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_s	Continuous source current (body diode)		-	-	55	A
I_{SM}	Pulsed source current (body diode)		-	-	220	A
V_{SD}	Diode forward voltage	$I_F = 25 \text{ A}; V_{GS} = 0 \text{ V}$ $I_F = 55 \text{ A}; V_{GS} = 0 \text{ V}$	-	0.9 1.0	1.2	V
t_{rr} Q_{rr}	Reverse recovery time Reverse recovery charge	$I_F = 20 \text{ A}; -dI_F/dt = 100 \text{ A}/\mu\text{s};$ $V_{GS} = 0 \text{ V}; V_R = 25 \text{ V}$	-	87 0.1	-	ns μC

Normalised Power Derating, PD (%)

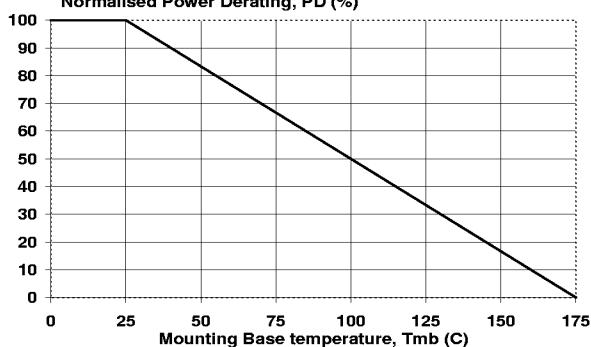


Fig.1. Normalised power dissipation.
 $PD\% = 100 \cdot P_D / P_{D, 25^\circ\text{C}} = f(T_{mb})$

Peak Pulsed Drain Current, I_{DM} (A)

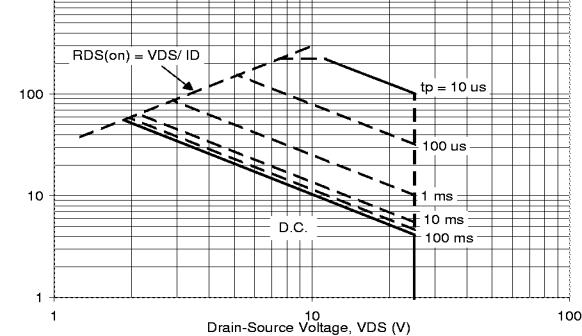


Fig.3. Safe operating area

I_D & $I_{DM} = f(V_{DS})$; I_{DM} single pulse; parameter t_p

Normalised Current Derating, ID (%)

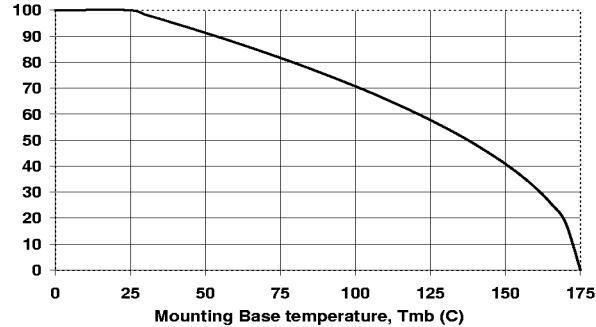


Fig.2. Normalised continuous drain current.
 $ID\% = 100 \cdot I_D / I_{D, 25^\circ\text{C}} = f(T_{mb})$; $V_{GS} \geq 5 \text{ V}$

Transient thermal impedance, $Z_{th,j-mb}$ (K/W)

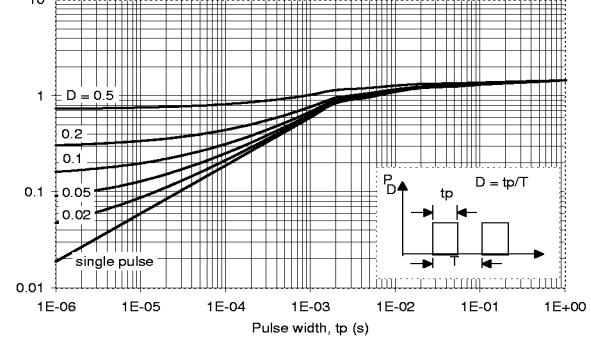


Fig.4. Transient thermal impedance.
 $Z_{th,j-mb} = f(t);$ parameter $D = t_p/T$

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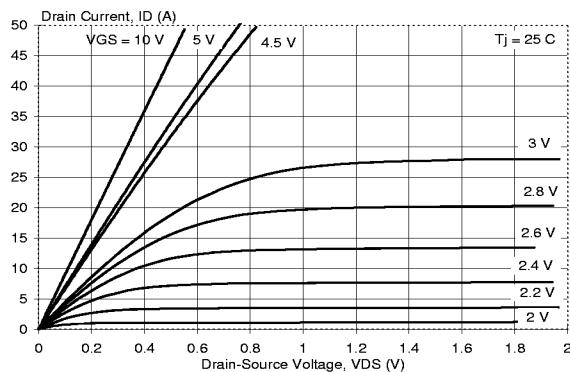


Fig.5. Typical output characteristics, $T_j = 25^\circ\text{C}$.
 $I_D = f(V_{DS})$; parameter V_{GS}

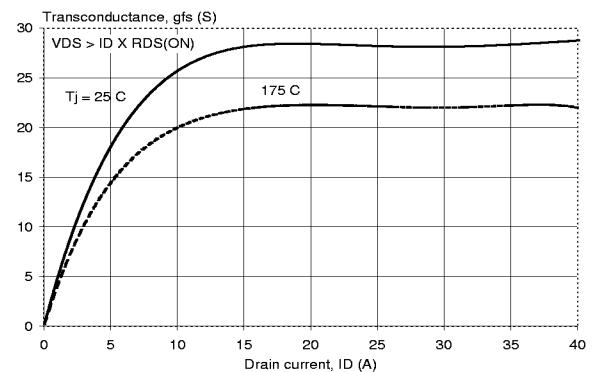


Fig.8. Typical transconductance, $T_j = 25^\circ\text{C}$.
 $g_{fs} = f(I_D)$; conditions: $V_{DS} = 25\text{ V}$

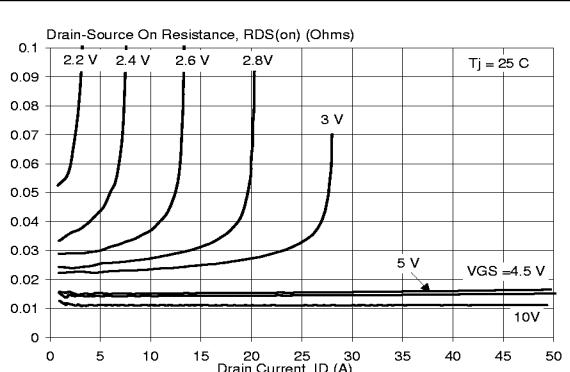


Fig.6. Typical on-state resistance, $T_j = 25^\circ\text{C}$.
 $R_{DS(\text{ON})} = f(I_D)$; parameter V_{GS}



Fig.9. Normalised drain-source on-state resistance.
 $A = R_{DS(\text{ON})}/R_{DS(\text{ON})25^\circ\text{C}} = f(T_j)$

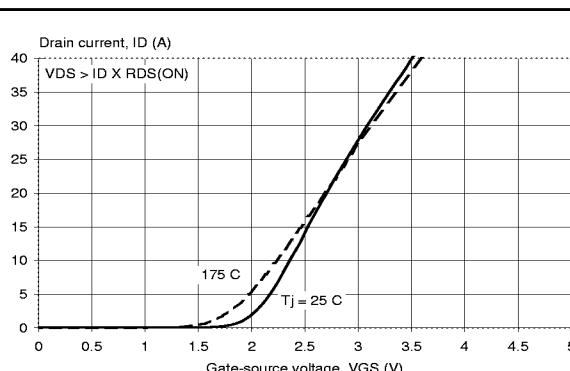


Fig.7. Typical transfer characteristics.
 $I_D = f(V_{GS})$; conditions: $V_{DS} = 25\text{ V}$; parameter T_j

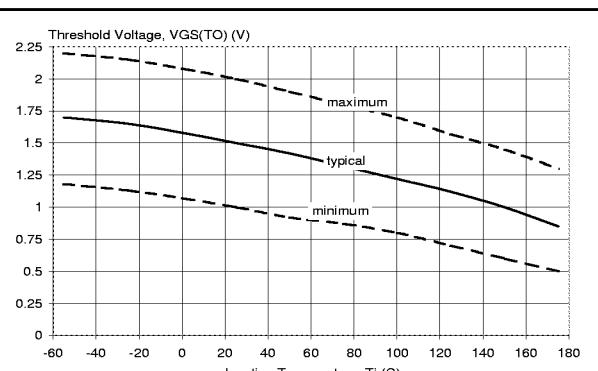


Fig.10. Gate threshold voltage.
 $V_{GS(\text{TO})} = f(T_j)$; conditions: $I_D = 1\text{ mA}$; $V_{DS} = V_{GS}$

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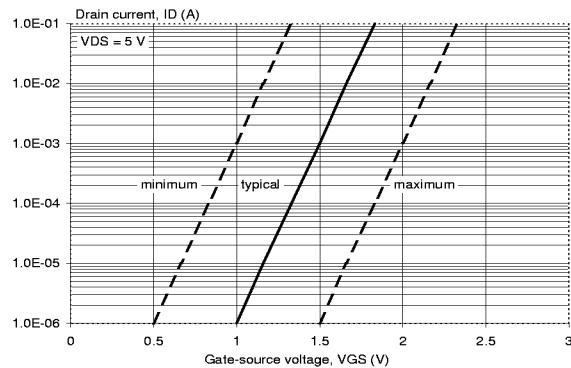


Fig.11. Sub-threshold drain current.
 $I_D = f(V_{GS})$; conditions: $T_j = 25^\circ\text{C}$; $V_{DS} = V_{GS}$

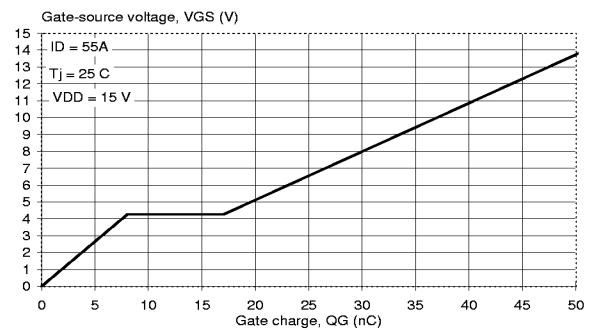


Fig.13. Typical turn-on gate-charge characteristics.
 $V_{GS} = f(Q_G)$; parameter V_{DS}

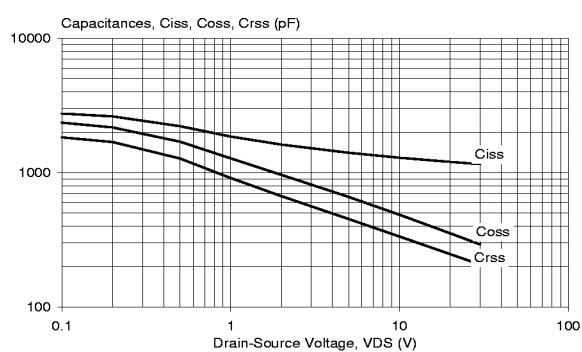


Fig.12. Typical capacitances, C_{iss} , C_{oss} , C_{rss} .
 $C = f(V_{DS})$; conditions: $V_{GS} = 0\text{ V}$; $f = 1\text{ MHz}$

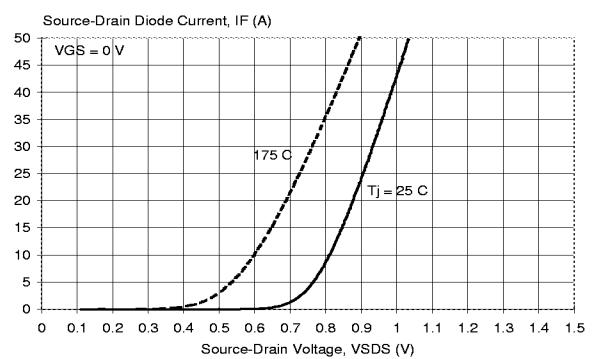


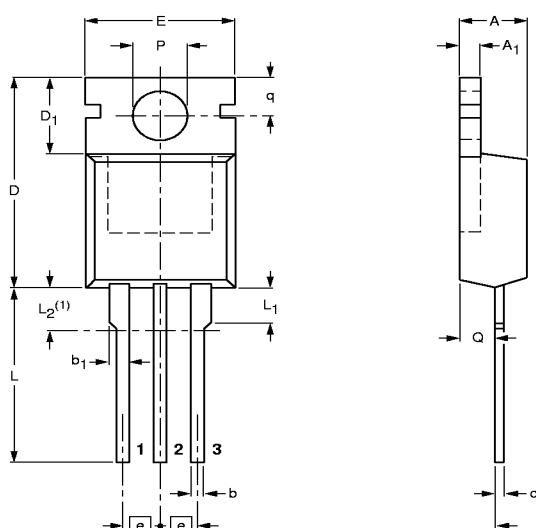
Fig.14. Typical reverse diode current.
 $I_F = f(V_{SDS})$; conditions: $V_{GS} = 0\text{ V}$; parameter T_j

N-channel TrenchMOS™ transistor
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MECHANICAL DATA

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220 SOT78



0 5 10 mm
scale

DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁	c	D	D ₁	E	e	L	L ₁	L ₂₍₁₎ max.	P	q	Q
mm	4.5 4.1	1.39 1.27	0.9 0.7	1.3 1.0	0.7 0.4	15.8 15.2	6.4 5.9	10.3 9.7	2.54 2.79	15.0 13.5	3.30 2.79	3.0	3.8 3.6	3.0 2.7	2.6 2.2

Note

1. Terminals in this zone are not tinned.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT78		TO-220			97-06-11

Fig.15. SOT78 (TO220AB); pin 2 connected to mounting base (Net mass:2g)

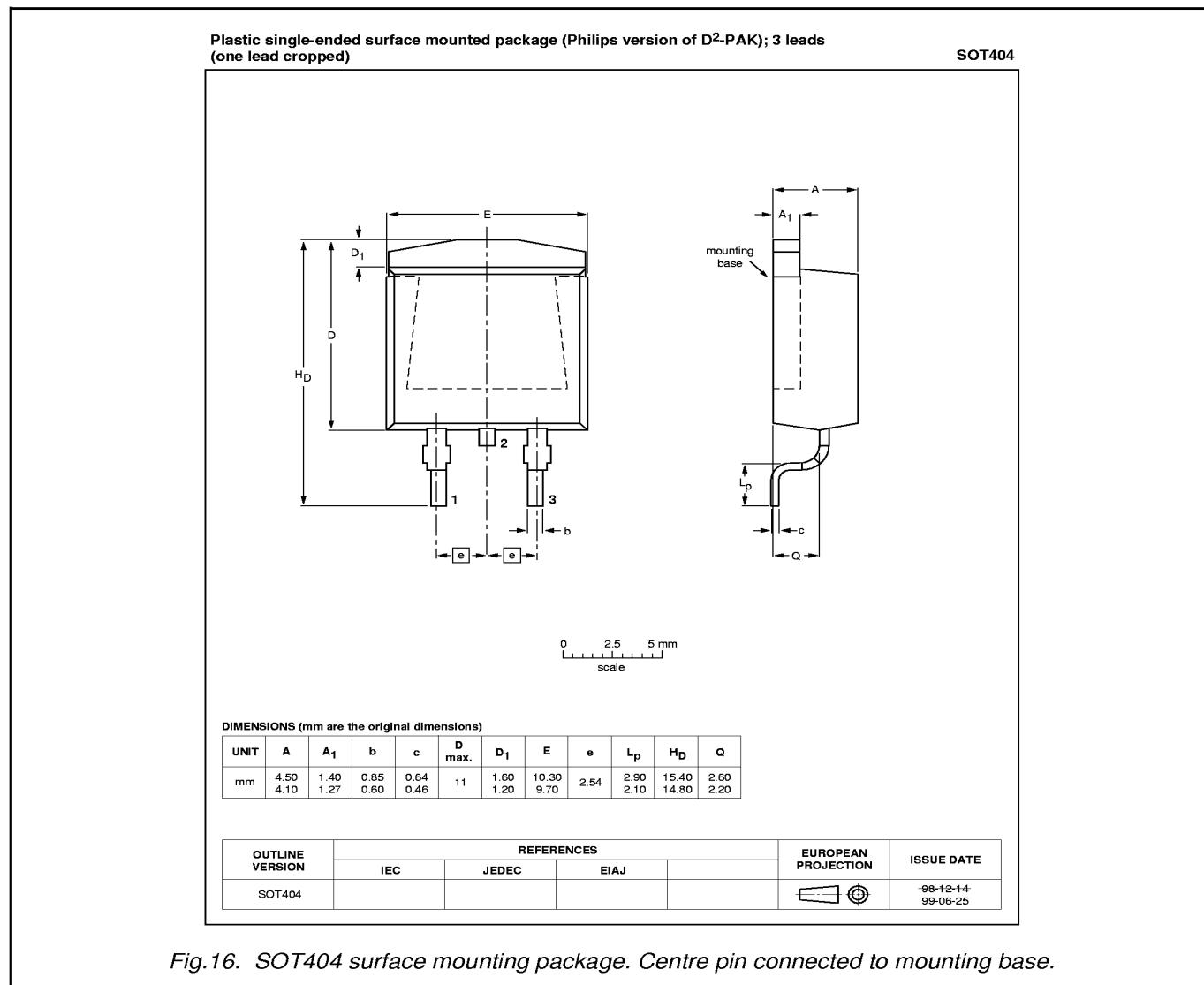
Notes

- This product is supplied in anti-static packaging. The gate-source input must be protected against static discharge during transport or handling.
- Refer to mounting instructions for SOT78 (TO220AB) package.
- Epoxy meets UL94 V0 at 1/8".

N-channel TrenchMOS™ transistor
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MECHANICAL DATA



Notes

1. This product is supplied in anti-static packaging. The gate-source input must be protected against static discharge during transport or handling.
2. Refer to SMD Footprint Design and Soldering Guidelines, Data Handbook SC18.
3. Epoxy meets UL94 V0 at 1/8".

N-channel TrenchMOS™ transistor
Logic level FET

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PHD55N03LT

MOUNTING INSTRUCTIONS

Dimensions in mm

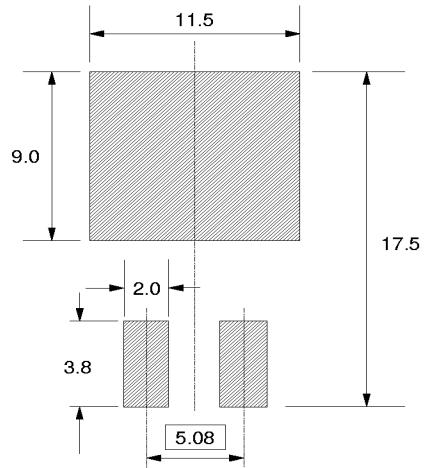
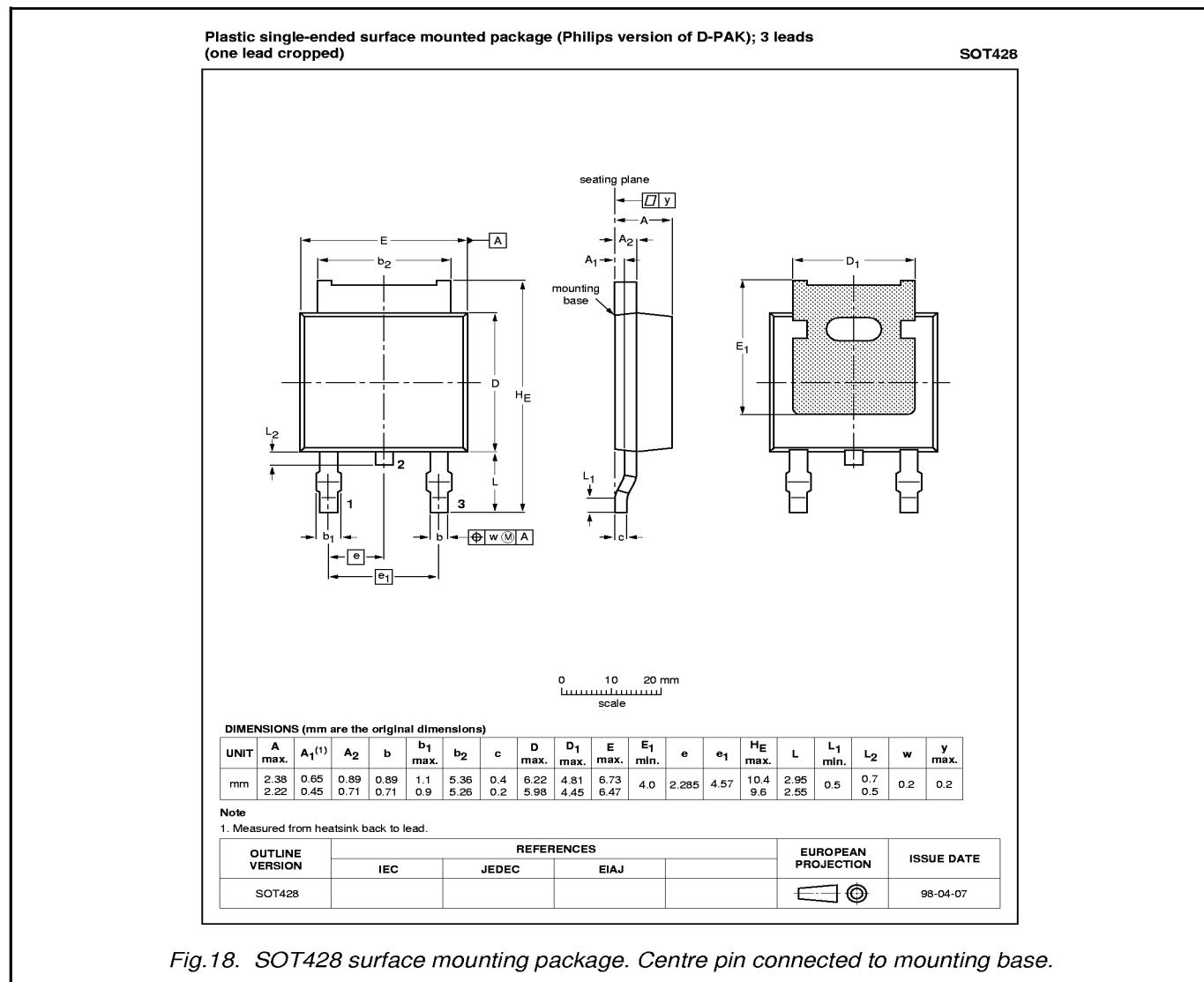


Fig.17. SOT404 : soldering pattern for surface mounting.

**N-channel TrenchMOS™ transistor
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**PHP55N03LT, PHB55N03LT
PHD55N03LT**
MECHANICAL DATA

Notes

1. This product is supplied in anti-static packaging. The gate-source input must be protected against static discharge during transport or handling.
2. Refer to SMD Footprint Design and Soldering Guidelines, Data Handbook SC18.
3. Epoxy meets UL94 V0 at 1/8".

N-channel TrenchMOS™ transistor
Logic level FET

PHP55N03LT, PHB55N03LT
PHD55N03LT

MOUNTING INSTRUCTIONS

Dimensions in mm

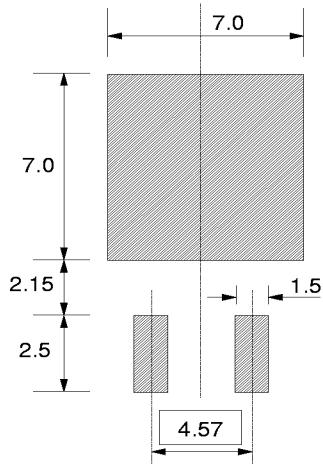


Fig.19. SOT428 : soldering pattern for surface mounting.

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	
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